

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device having a portion thereof formed from a wafer of semiconductive material by a laser etching process comprising: providing a substrate of semiconductive wafer material having a surface; and forming resist on at least a portion of the surface of the substrate of semiconductive wafer material having a portion thereof removed by; and etching the resist from the surface of the substrate using a laser forming a roughened surface on the surface of the substrate.
2. (Currently Amended) The semiconductor device method according to claim 1, wherein the laser comprises a laser associated with an automolding system.
3. (Currently Amended) The semiconductor device method according to claim 1, wherein the laser includes one of an Nd:YAG laser and an excimer laser.
4. (Currently Amended) The semiconductor device method-according to claim 1, wherein the substrate comprises a ball-grid-array substrate.
5. (Currently Amended) The semiconductor device method according to claim 1, further comprising a vision system for detecting the resist.
6. (Currently Amended) The semiconductor device method according to claim 5, wherein the vision system comprises: providing a laser scanning system; and for detecting changes in a pattern of the substrate.
7. (Currently Amended) A method of enhancing the adhesion of a compound to a surface of a substrate comprising: providing the substrate having the surface; and

roughening the surface of the substrate using a laser to remove material from the surface of the substrate.

8. (Previously Presented) The method according to claim 7, wherein roughening comprises removing contamination and foreign particles from the surface of the substrate.

9. (Withdrawn) An automolding system comprising:  
providing a substrate having a surface;  
preheating the substrate;  
forming a resist layer;  
baking the substrate; and  
removing contaminants from the substrate using a laser.

10. (Withdrawn) The automolding system of claim 9, wherein the laser comprises one of an Nd:YAG laser and an excimer laser.

11. (Withdrawn) The automolding system of claim 9, further comprising:  
placing the substrate in a mold; and  
encapsulating the substrate.

12. (Currently Amended) A semiconductor device having a portion formed by a laser etching process on a substrate of semiconductive material having a surface comprising:  
forming resist located on at least a portion of the surface; and having a portion thereof removed  
by etching the resist from the at least a portion of the surface of the substrate using a laser  
forming a roughened surface on the surface of the substrate of semiconductive material.

13. (Currently Amended) The semiconductor device method according to claim 12,  
wherein the laser comprises a laser associated with an automolding system.

14. (Currently Amended) The semiconductor device method according to claim 12, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

15. (Currently Amended) The semiconductor device method according to claim 12, wherein the substrate comprises a ball-grid-array substrate.

16. (Currently Amended) The semiconductor device method according to claim 12, further comprising a vision system for detecting the resist.

17. (Currently Amended) The semiconductor device method according to claim 16, wherein the vision system comprises:

providing a laser scanning system; and for detecting changes in a pattern of the substrate.